

JBH:jiv 11/01/01 6047-55230

KLARQUIST SPARKMAN, LLP

16th Floor World Trade Center, 121 S.W. Salmon Street, Portland, Oregon 97204 U.S.A.

PHONE: 503-226-7391 FAX: 503-228-9446

PLEASE DELIVER DIRECTLY TO EXAMINER S. RAO

Fax No.: 703/746-3926

Total No. Pages: 3 including this cover sheet

Message: Transmitted herewith for filing in the above-identified application is a REQUEST FOR INTERVIEW. If you do not receive all pages or if you have problems receiving transmittal, please call Jeffrey B. Haendler, Esq. at (503) 226-7391. The fee (large entity) has been calculated as shown below.

In re application of: Gilton et al.

Application No.: 09/579,345

Filed: May 25, 2000

For: SEMICONDUCTOR FABRICATION
METHODS AND APPARATUS

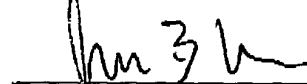
Examiner: S. Rao

Art Unit: 2814

Date: November 1, 2001

CERTIFICATE OF FACSIMILE

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Jeffrey B. Haendler, Esq.
Attorney for Applicants

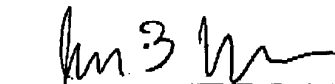
FEE CALCULATION FOR CLAIMS AS AMENDED

For	No. after amendment	No. paid for previously	Extra	Rate	Fee
Total Claims	38	- 38*	= 0	\$18.00	\$ 0.00
Indep. Claims	12	- 12**	= 0	\$84.00	\$ 0.00
TOTAL FEE FOR THIS AMENDMENT					\$ 0.00

*greater of twenty or number for which fee has been paid. **greater of three or number for which fee has been paid.

- ☒ No additional fee is required.
☒ Please charge any fees that may be required in connection with filing of this Request for Interview to Deposit Account 02-4550.

DATED: November 1, 2001



Jeffrey B. Haendler
Registration No. 43,652

cc: Docketing

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Attorney Reference No. 6047-55230
Application No. 09/579,345
PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of: Gilton et al.

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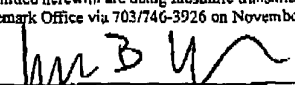
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CERTIFICATE OF FACSIMILE

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Jeffrey B. Haendler, Esq.
Attorney for ApplicantREQUEST FOR INTERVIEW

Applicants' attorney respectfully requests a telephone interview to discuss at least the following issues regarding the Office action (Action) dated October 10, 2001:

- On page 2 of the Action, the Examiner contends that Hawthorne, at col. 4, lines 60-67, discloses a "solvent vapor as including a hydrous material such as water." However, this portion of Hawthorne discusses filling a chamber with water and an etching agent, not a solvent vapor. ✓
- On page 4 of the Action, the Examiner indicates that the isopropyl alcohol of Hawthorne is equivalent to the reactant gas of claim 14. If the isopropyl alcohol is the vaporized solvent (as stated at the bottom of page 3 of the Action), then it cannot be the reactant gas. *fine*
- Point No. 3 on page 4 of the Action requires further explanation. Nowhere in Hawthorne (including the cited col. 4, line 60 through col. 5, line 1 and col. 5, lines 11-14), is there support for incorporating a reactant gas into a vaporized solvent. The first cited passage (col. 4, line 60 through col. 5, line 1) discusses injecting water and an etching agent into the chamber. The second cited passage (col. 5, lines 11-14) discusses introducing vaporized isopropyl alcohol into the chamber. Thus, there is only one vaporous or gaseous fluid in Hawthorne's process- the isopropyl alcohol. In short, it is not clear which fluids disclosed in Hawthorne the Examiner alleges are equivalent to (1) the vaporized "liquid solvent" and (2) the "reactant gas" recited in Applicants' claim 14. *see*

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• On page 5 of the Action, the Examiner apparently contends that the hydrous material condenses as it comes into contact with the wafer. Since Hawthorne does not teach vaporizing water, it necessarily does not teach condensing water. *See 8 lines 15-20*

• On page 5 of the Action, the Examiner discusses col. 4, lines 47-50 of Hawthorne. This passage is not relevant as it applies to claim 14. Film 26 shown in FIG. 3 of Hawthorne does not comprise a previously vaporized solvent. Film 26 is a layer of material, such as silicon, polysilicon, or nitride, that is to be etched. See col. 4, lines 19-27 of Hawthorne.

• On page 6, the Examiner states that "the heated solvent vapor has to flow through the thin layer of liquid solvent." A heated vapor, that condenses upon contact with a cooler surface (as stated elsewhere in the Action by the Examiner), cannot then flow through a liquid layer (assuming *arguendo* there is one) in a gaseous or vaporous state.

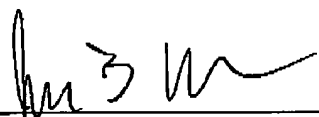
• With respect to claim 24, the Examiner states on page 5 of the Action that Imuro describes supplying heated water to a wafer surface that is cooler than the water. However, Imuro describes heating a wafer surface. There is absolutely no support for the Examiner's contention that the wafer surface in Imuro is at a temperature that is less than the temperature of the heated water.

It is believed that a telephone interview to discuss the issues outlined above will facilitate allowance of the application. The Examiner is requested to telephone the undersigned attorney at his earliest convenience to schedule such an interview.

Respectfully submitted,

KLARQUIST SPARKMAN, LLP

By


Jeffrey B. Haendler
Registration No. 43,652

One World Trade Center, Suite 1600
121 S.W. Salmon Street
Portland, Oregon 97204
Telephone: (503) 226-7391
Facsimile: (503) 228-9446